Silicon NPN Power Transistors 2SD1375

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- High power dissipation

APPLICATIONS

- Designed for line operated audio output amplifier ,and switching power supply drivers applications

Fig.1 simplified outline (TO-3) and symbol

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		4	A
P_C	Collector power dissipation	T_C=75℃	90	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors 2SD1375

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=30mA ;I_B=0	300			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.6A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A; I_B=0.6A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=300V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	30			

Silicon NPN Power Transistors 2SD1375

PACKAGE OUTLINE

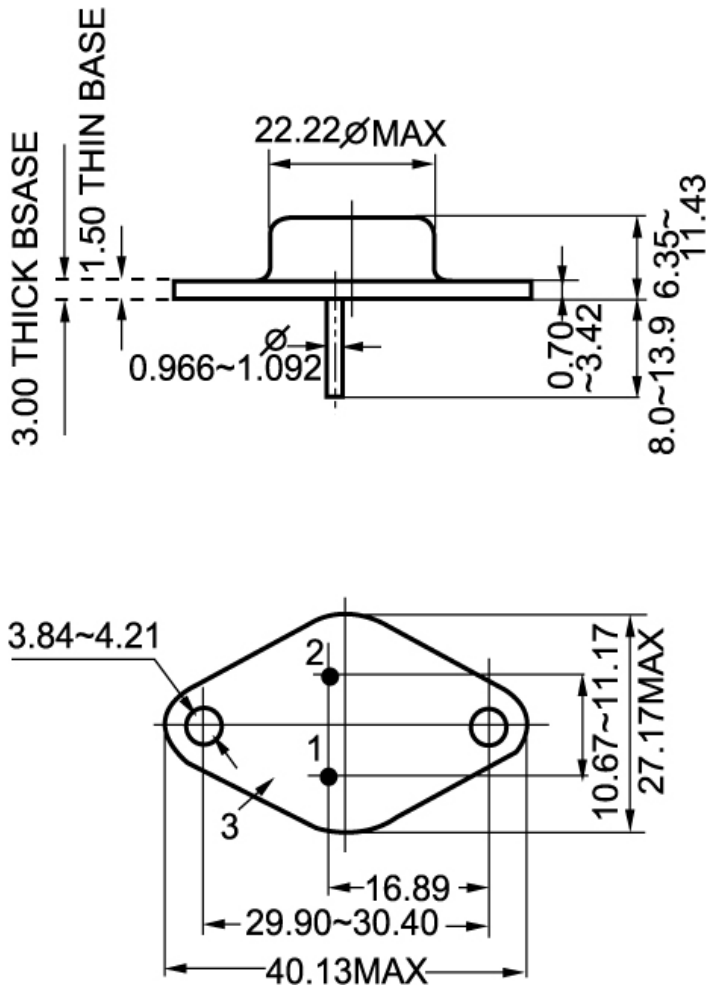

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)